

Operational Amplifier, Rail-to-Rail, Low Input Bias Current, 1.8 V to 5 V Single-Supply

LMV301

The LMV301 CMOS operational amplifier can operate over a power supply range from 1.8 V to 5 V and has a quiescent current of less than 200 μA , maximum, making it ideal for portable battery–operated applications such as notebook computers, PDA's and medical equipment. Low input bias current and high input impedance make it highly tolerant of high source–impedance signal–sources such as photodiodes and pH probes. In addition, the LMV301's excellent rail–to–rail performance will enhance the signal–to–noise performance of any application together with an output stage capable of easily driving a 600 Ω resistive load and up to 1000 pF capacitive load.

Features

- Single Supply Operation (or $\pm V_S/2$)
- Vs from 1.8 V to 5 V
- Low Quiescent Current: 185 μ A, Max with $V_S = 1.8 \text{ V}$
- Rail-to-Rail Output Swing
- Low Bias Current: 35 pA, max
- No Output Phase–Reversal when the Inputs are Overdriven
- These are Pb-Free Devices

Typical Applications

- Portable Battery-Powered Instruments
- Notebook Computers and PDAs
- Cell Phones and Mobile Communication
- Digital Cameras
- Photodiode Amplifiers
- Transducer Amplifiers
- Medical Instrumentation
- Consumer Products



SC70-5 SQ SUFFIX CASE 419A STYLES 3

MARKING DIAGRAM



LMV301 = Specific Device Code

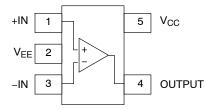
M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN CONNECTION



STYLE 3 PINOUT

ORDERING INFORMATION

See detailed ordering and shipping information in the dimensions section on page 11 of this data sheet.

MAXIMUM RATINGS

Symbol	Rating	Value	Unit
Vs	Power Supply (Operating Voltage Range V _S = 1.8 V to 5.0 V)	5.5	V
V_{IDR}	Input Differential Voltage	±Supply Voltage	V
V _{ICR}	Input Common Mode Voltage Range	-0.5 to (V+) + 0.5	V
	Maximum Input Current	10	mA
t _{So}	Output Short Circuit (Note 1)	Continuous	
T_J	Maximum Junction Temperature (Operating Range -40°C to 85°C)	150	°C
J_A	Thermal Resistance (5-Pin SC70-5)	280	°C/W
T _{stg}	Storage Temperature	-65 to 150	°C
	Mounting Temperature (Infrared or Convection (30 sec))	260	
V _{ESD}	ESD Tolerance Machine Model Human Body Model	100 1500	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality

should not be assumed, damage may occur and reliability may be affected.

1. Continuous short–circuit to ground operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of 45 mA over long term may adversely affect reliability. Also, shorting output to V+ will adversely affect reliability; likewise shorting output to V- will adversely affect reliability.

1.8 V DC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V_{CC} = 1.8 V, R_L = 1 $M\Omega$, V_{EE} = 0 V, V_O = $V_{CC}/2$)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		1.7	9	mV
Input Offset Voltage Average Drift	T_CV_{IO}	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		5		μV/°C
Input Bias Current (Note 2)	Ι _Β			3	35	pA
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			50	
Common Mode Rejection Ratio	CMRR	$0 \text{ V} \leq \text{V}_{\text{CM}} \leq 0.9 \text{ V}$	50	63		dB
Power Supply Rejection Ratio	PSRR	$1.8 \text{ V} \le \text{V}_{CC} \le 5 \text{ V}, \\ \text{V}_{O} = 1 \text{ V}, \text{V}_{CM} = 1 \text{ V}$	62	100		dB
Input Common-Mode Voltage Range	V _{CM}	For CMRR ≥ 50 dB	0 to 0.9	-0.2 to 0.9		V
Large Signal Voltage Gain (Note 2)	A _V	$R_L = 600\Omega$	83	100		dB
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	80			
		$R_L = 2 k\Omega$	83	100		
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	80			
Output Swing	V _{OH}	$R_L = 600 \Omega \text{ to } 0.9 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	1.65 1.63			V
	V _{OL}	$R_L = 600 \Omega \text{ to } 0.9 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$		75	100 120	mV
	V _{OH}	$R_L = 2 k\Omega \text{ to } 0.9 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	1.5 1.4	1.76		V
	V _{OL}	$R_L = 2 \text{ k}\Omega \text{ to } 0.9 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$		25	35 40	mV
Output Short Circuit Current (Note 2)	Io	Sourcing = $V_O = 0 V$ Sinking = $V_O = 1.8 V$	10 20	60 160		mA
Supply Current	I _{CC}	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			185	μΑ

1.8 V AC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V_{CC} = 1.8 V, R_L = 1 $M\Omega$, V_{EE} = 0 V, V_O = $V_{CC}/2$)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Slew Rate	S _R			1		V/μs
Gain Bandwidth Product	GBWP	C _L = 200 pF		1		MHz
Phase Margin	Θ_{m}			60		0
Gain Margin	G _m			10		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz		50		nV/√ Hz
Total Harmonic Distortion	THD	$A_V = +1, V - 1 V_{PP},$ $R_L = 10 \text{ kW, f} = 1 \text{ kHz}$		0.01		%

^{2.} Guaranteed by design and/or characterization.

2.7 V DC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V_{CC} = 2.7 V, R_L = 1 $M\Omega$, V_{EE} = 0 V, V_O = $V_{CC}/2$)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		1.7	9	mV
Input Offset Voltage Average Drift	T_CV_{IO}	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		5		μV/°C
Input Bias Current (Note 2)	Ι _Β			3	35	pА
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			50	
Common Mode Rejection Ratio	CMRR	$0 \text{ V} \leq \text{V}_{\text{CM}} \leq 1.35 \text{ V}$	50	63		dB
Power Supply Rejection Ratio	PSRR	$1.8 \text{ V} \le \text{V}_{CC} \le 5 \text{ V}, \\ \text{V}_{O} = 1 \text{ V}, \text{V}_{CM} = 1 \text{ V}$	62	100		dB
Input Common-Mode Voltage Range	V _{CM}	For CMRR ≥ 50 dB	0 to 1.35	-0.2 to1.35		V
Large Signal Voltage Gain (Note 2)	A _V	$R_L = 600 \Omega$	83	100		dB
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	80			
		$R_L = 2 k\Omega$	83	100		
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	80			
Output Swing	V _{OH}	$R_L = 600 \Omega \text{ to } 1.35 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	2.55 2.53	2.62		V
	V _{OL}	$R_L = 600 \Omega \text{ to } 1.35 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$		78	100 280	mV
	V _{OH}	$R_L = 2 \text{ k}\Omega \text{ to } 1.35 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	2.65 2.64	2.675		V
	V _{OL}	$R_L = 2 \text{ k}\Omega \text{ to } 1.35 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$		75	100 110	mV
Output Short Circuit Current (Note 2)	Io	Sourcing = $V_O = 0 V$ Sinking = $V_O = 2.7 V$	10 20	60 160		mA
Supply Current	I _{CC}	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			185	μΑ

2.7 V AC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V_{CC} = 2.7 V, P_C = 1 M Ω , P_C = 0 V, P

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Slew Rate	S _R			1		V/μs
Gain Bandwidth Product	GBWP	C _L = 200 pF		1		MHz
Phase Margin	Θ_{m}			60		0
Gain Margin	G _m			10		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz		50		nV/√Hz
Total Harmonic Distortion	THD	$A_V = +1, V - 1 V_{PP},$ $R_L = 10 \text{ kW, f} = 1 \text{ kHz}$		0.01		%

^{2.} Guaranteed by design and/or characterization.

5.0 V DC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V_{CC} = 5.0 V, R_L = 1 M Ω , V_{EE} = 0 V, V_O = $V_{CC}/2$)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		1.7	9	mV
Input Offset Voltage Average Drift	T_CV_{IO}	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		5		μV/°C
Input Bias Current (Note 2)	I _B			3	35	pА
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			50	1
Common Mode Rejection Ratio	CMRR	$0 \text{ V} \leq \text{V}_{\text{CM}} \leq 4 \text{ V}$	50	63		dB
Power Supply Rejection Ratio	PSRR	$1.8 \text{ V} \le \text{V}_{CC} \le 5 \text{ V}, \\ \text{V}_{O} = 1 \text{ V}, \text{V}_{CM} = 1 \text{ V}$	62	100		dB
Input Common-Mode Voltage Range	V _{CM}	For CMRR ≥ 50 dB	0 to 4	-0.2 to 4.2		V
Large Signal Voltage Gain (Note 2)	A _V	$R_L = 600 \Omega$	83	100		dB
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	80			
		$R_L = 2 k\Omega$	83	100		
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	80			
Output Swing	V _{OH}	$R_L = 600 \Omega \text{ to } 2.5 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	4.850 4.840			V
	V _{OL}	$R_L = 600 \Omega \text{ to } 2.5 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			150 160	mV
	V _{OH}	$R_L = 2 k\Omega \text{ to } 2.5 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	4.935 4.900			V
	V _{OL}	$R_L = 2 k\Omega \text{ to } 2.5 \text{ V}$ $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			65 75	mV
Output Short Circuit Current (Note 2)	Io	Sourcing = $V_O = 0 V$ Sinking = $V_O = 5 V$	10 10	60 160		mA
Supply Current	I _{CC}	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			200	μA

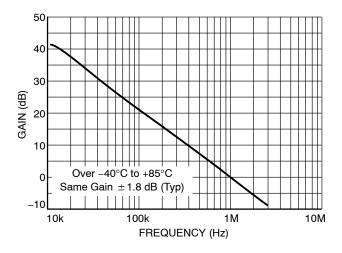
5.0 V AC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for T_A = 25°C, V_{CC} = 5.0 V, P_C = 1 M Ω , P_C = 0 V, P

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Slew Rate	S _R			1		V/μs
Gain Bandwidth Product	GBWP	C _L = 200 pF		1		MHz
Phase Margin	Θ_{m}			60		0
Gain Margin	G _m			10		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz		50		nV/√Hz
Total Harmonic Distortion	THD	$A_V = +1, V - 1 V_{PP},$ $R_L = 10 \text{ kW, f} = 1 \text{ kHz}$		0.01		%

^{2.} Guaranteed by design and/or characterization.

TYPICAL CHARACTERISTICS

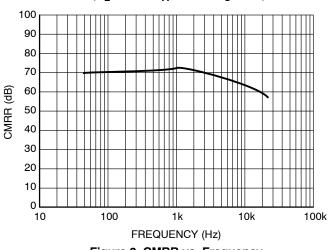
 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$



100 90 80 80 70 40 10k 100k 1M 10N FREQUENCY (Hz)

Figure 1. Open Loop Frequency Response (R_L = 2 k Ω , T_A = 25°C, V_S = 5 V)

Figure 2. Open Loop Phase Margin ($R_L = 2 \text{ k}\Omega, T_A = 25^{\circ}\text{C}$)



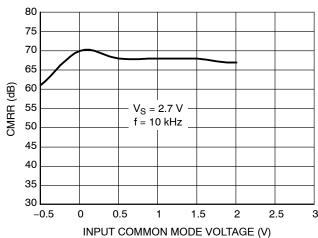
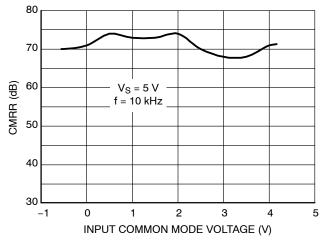


Figure 3. CMRR vs. Frequency (R_L = 5 k Ω , V_S = 5 V)

Figure 4. CMRR vs. Input Common Mode Voltage



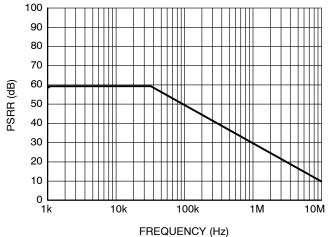
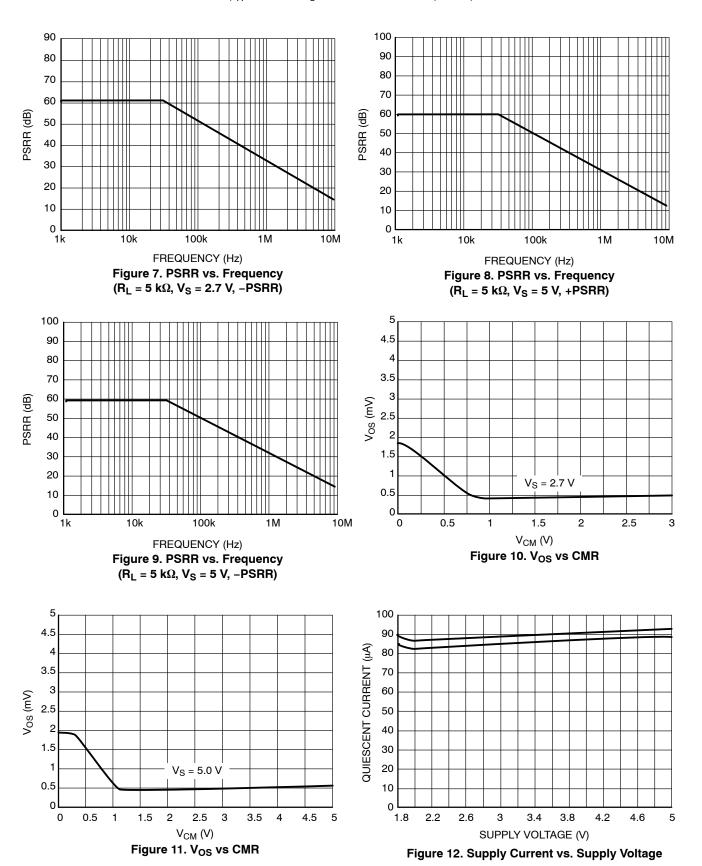


Figure 5. CMRR vs. Input Common Mode Voltage

Figure 6. PSRR vs. Frequency ($R_L = 5 \text{ k}\Omega$, $V_S = 2.7 \text{ V}$, +PSRR)

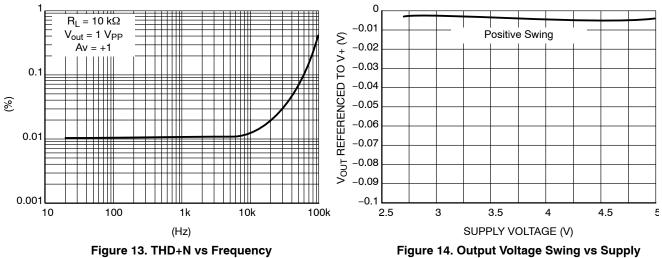
TYPICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$



TYPICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$



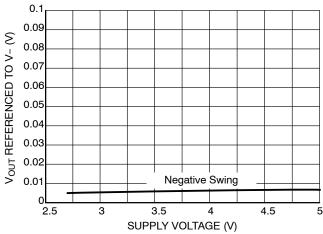
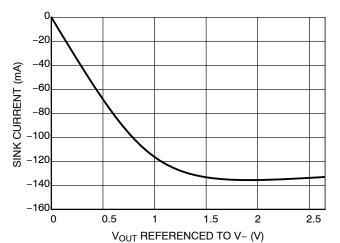


Figure 15. Output Voltage Swing vs Supply Voltage (R_L = 10k)



Voltage (R_L = 10k)

Figure 16. Sink Current vs. Output Voltage $V_S = 2.7 V$

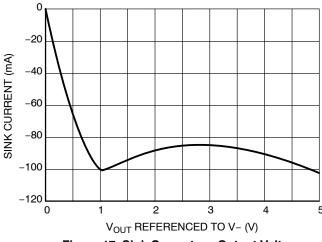


Figure 17. Sink Current vs. Output Voltage $V_S = 5.0 V$

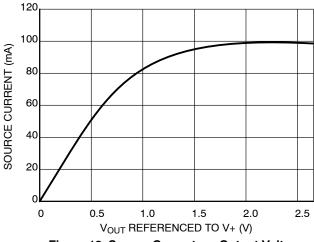


Figure 18. Source Current vs. Output Voltage $V_{S} = 2.7 V$

TYPICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$

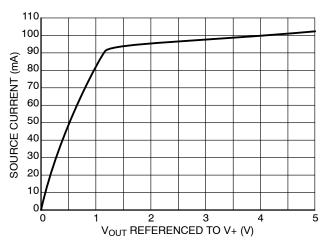


Figure 19. Source Current vs. Output Voltage $V_S = 5.0 \text{ V}$

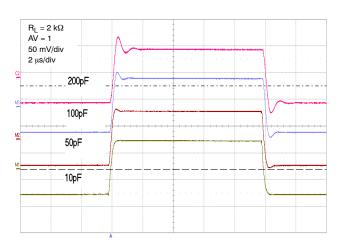


Figure 20. Settling Time vs. Capacitive Load

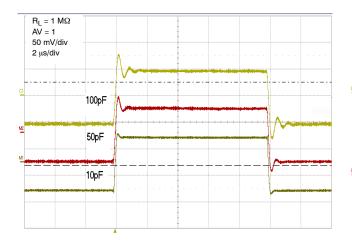


Figure 21. Settling Time vs. Capacitive Load

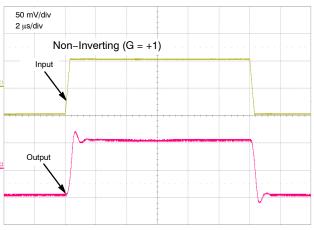


Figure 22. Step Response – Small Signal

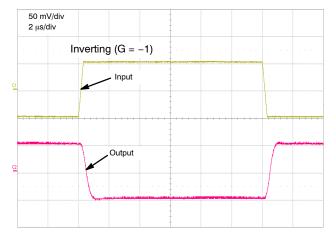


Figure 23. Step Response - Small Signal

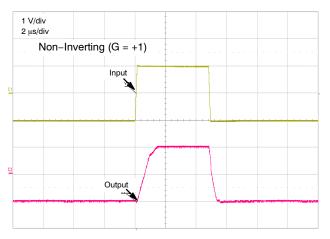


Figure 24. Step Response - Large Signal

TYPICAL CHARACTERISTICS

($T_A = 25^{\circ}C$ and $V_S = 5 V$ unless otherwise specified)

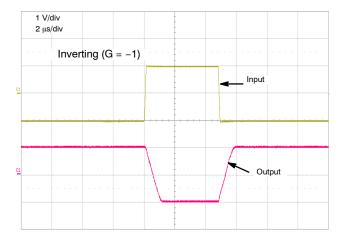


Figure 25. Step Response – Large Signal

APPLICATIONS

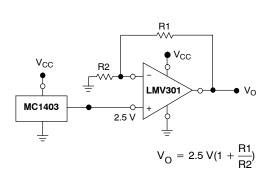


Figure 26. Voltage Reference

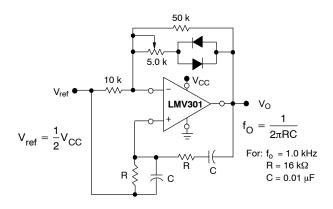


Figure 27. Wien Bridge Oscillator

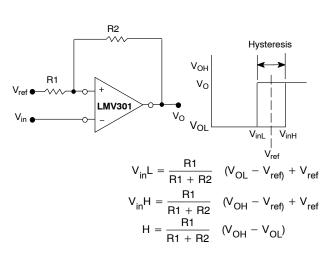
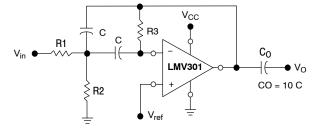


Figure 28. Comparator with Hysteresis



Given: f_0 = center frequency $A(f_0)$ = gain at center frequency

Choose value
$$f_o$$
, $\frac{C}{Q}$
Then: $R3 = \frac{Q}{\pi f_O C}$
$$R1 = \frac{R3}{2 \, A(f_O)}$$

$$R2 = \frac{R1 \, R3}{4 \, Q^2 \, R1 - R3}$$

For less than 10% error from operational amplifier, $((Q_O f_O)/BW) < 0.1$ where f_o and BW are expressed in Hz. If source impedance varies, filter may be preceded with voltage follower buffer to stabilize filter parameters.

Figure 29. Multiple Feedback Bandpass Filter

ORDERING INFORMATION

Device	Pinout Style	Marking	Package	Shipping [†]
LMV301SQ3T2G	Style 3	AAD	SC70-5 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

DATE 11 APR 2023

NOTES:

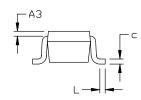
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 419A-01 DBSDLETE, NEW STANDARD 419A-02
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS,
 OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

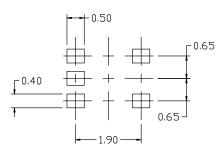
DIM	MILLIMETERS			
INITU	MIN.	N□M.	MAX.	
А	0.80	0.95	1.10	
A1			0.10	
A3		0.20 REF	•	
b	0.10	0.20	0.30	
C	0.10		0.25	
D	1.80	2.00	2,20	
Е	2.00	2.10	2.20	
E1	1.15	1.25	1.35	
е	0.65 BSC			
L	0.10	0.15	0.30	

5 4 E1 E1 E1 E1 E1 E1



◆ 0.2 M B M





RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

STYLE 1:
PIN 1. BASE
EMITTER
3. BASE
COLLECTOR
COLLECTOR

STYLE 2:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1 STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

STYLE 5: PIN 1. CATHODE 2. COMMON ANODE 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4

STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 8:
PIN 1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER

STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

DOCUMENT NUMBER:

98ASB42984B

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DESCRIPTION:

5. COLLECTOR 2/BASE 1

SC-88A (SC-70-5/SOT-353)

PAGE 1 OF 1

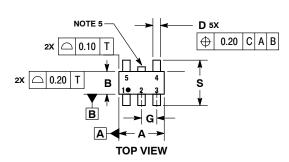
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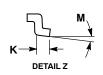


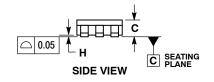


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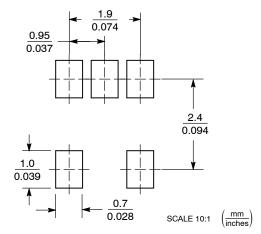


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- DIMENSIONING AND TOLERANCING PER ASME
 Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
 THICKNESS. MINIMUM LEAD THICKNESS IS THE
 MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A. OPTIONAL CONSTRUCTION: AN ADDITIONAL
- TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.85	3.15		
В	1.35	1.65		
С	0.90	1.10		
D	0.25	0.50		
G	0.95	BSC		
Н	0.01	0.10		
J	0.10	0.26		
K	0.20	0.60		
М	0 °	10 °		
S	2.50	3.00		

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*





XXX = Specific Device Code XXX = Specific Device Code

= Assembly Location = Date Code

= Year = Pb-Free Package

= Work Week W

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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